

Shantou Huashan Electronic Devices Co.,Ltd.

NPN DARLINGTON TRANSISTOR

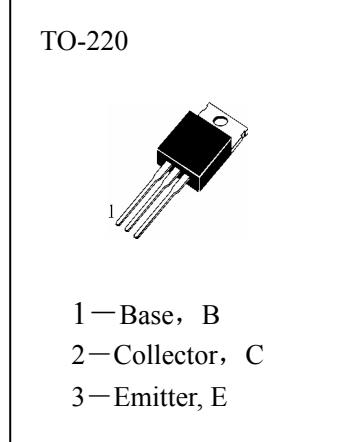
HP142TS

■ APPLICATIONS

High DC Current Gain

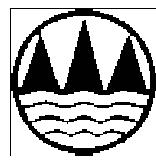
■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

| | |
|---|------------|
| T_{stg} —Storage Temperature..... | -55~150 °C |
| T_j —Junction Temperature..... | 150 °C |
| P_c —Collector Dissipation ($T_c=25^\circ\text{C}$) | 70W |
| V_{CBO} —Collector-Base Voltage..... | 100V |
| V_{CEO} —Collector-Emitter Voltage..... | 100V |
| V_{EBO} —Emitter-Base Voltage..... | 5V |
| I_c —Collector Current (DC) | 8A |
| I_B —Base Current..... | 0.5A |



■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

| Symbol | Characteristics | Min | Typ | Max | Unit | Test Conditions |
|-------------------------------|---------------------------------------|------|-----|-----|------|---|
| $BV_{\text{CEO}}(\text{SUS})$ | Collector-Emitter Sustaining Voltage | 100 | | | V | $I_C=30\text{mA}, I_B=0$ |
| I_{CEO} | Collector Cutoff Current | | 2 | | mA | $V_{\text{CE}}=50\text{V}, I_B=0$ |
| I_{CBO} | Collector Cutoff Current | | 1 | | mA | $V_{\text{CB}}=100\text{V}, I_E=0$ |
| I_{EBO} | Emitter-Base Cutoff Current | | 2 | | mA | $V_{\text{EB}}=5\text{V}, I_C=0$ |
| HFE (1) | DC Current Gain | 1000 | | | | $V_{\text{CE}}=4\text{V}, I_C=0.5\text{A}$ |
| HFE (2) | | 1000 | | | | $V_{\text{CE}}=4\text{V}, I_C=3\text{A}$ |
| $V_{\text{CE(sat1)}}$ | Collector- Emitter Saturation Voltage | | 2 | | V | $I_C=5\text{A}, I_B=10\text{mA}$ |
| $V_{\text{CE(sat2)}}$ | | | 3 | | V | $I_C=10\text{A}, I_B=40\text{mA}$ |
| $V_{\text{BE(sat)}}$ | Base- Emitter Saturation Voltage | | 3.5 | | V | $I_C=10\text{A}, I_B=40\text{mA}$ |
| $V_{\text{BE(on)}}$ | Base- Emitter On Voltage | | 3 | | V | $V_{\text{CE}}=4\text{V}, I_C=10\text{A},$ |
| t_D | Delay time | 0.15 | | | uS | $\left. \begin{array}{l} V_{\text{cc}}=30\text{V}, I_C=5\text{A} \\ I_{B1}=20\text{mA} \\ I_{B2}=-20\text{mA} \end{array} \right\}$ |
| t_R | Rise Time | 0.55 | | | uS | |
| t_S | Storage Time | 2.5 | | | uS | |
| t_F | Fall Time | 2.5 | | | uS | |



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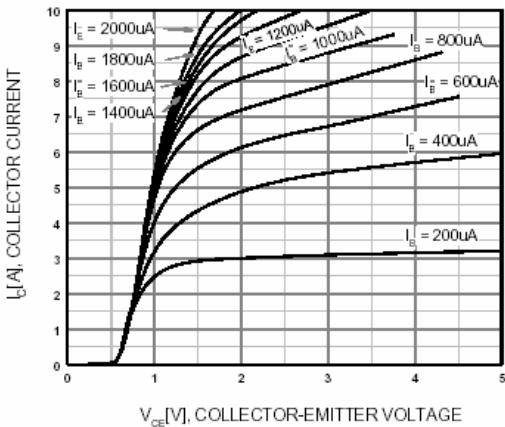


Figure 1. Static Characteristic

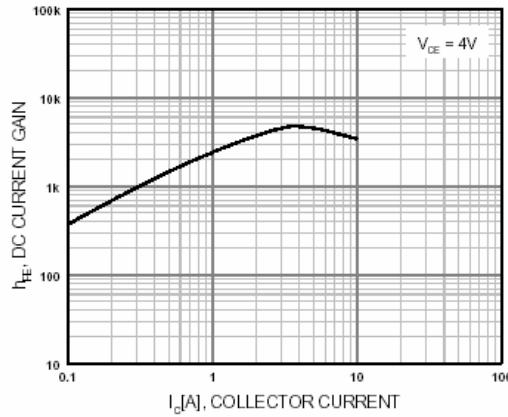


Figure 2. DC current Gain

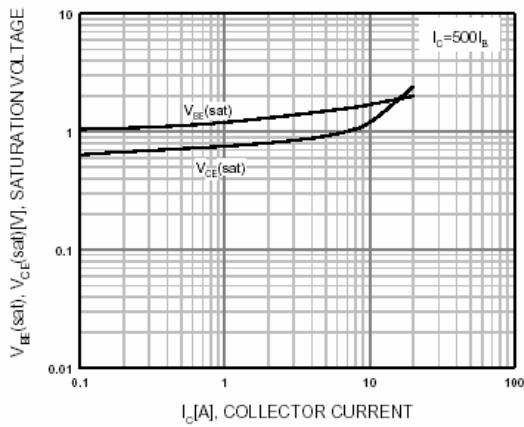


Figure 3. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

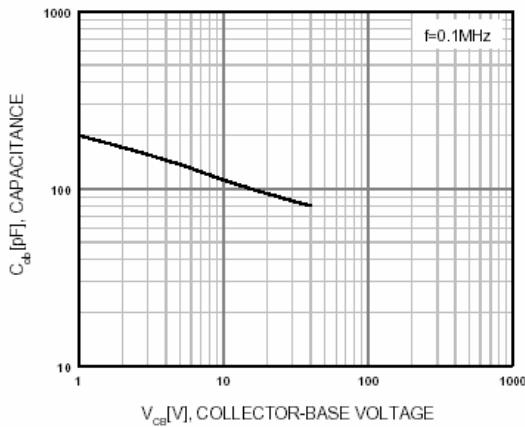


Figure 4. Collector Output Capacitance

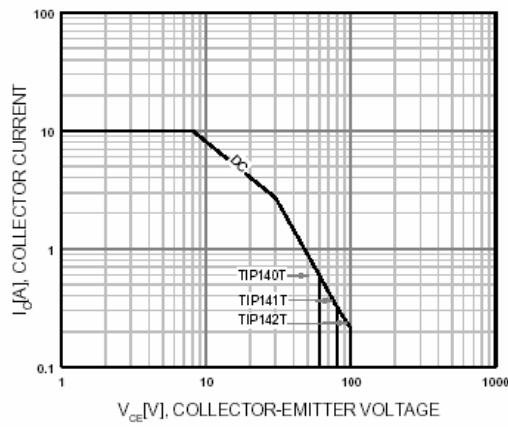


Figure 5. Safe Operating Area

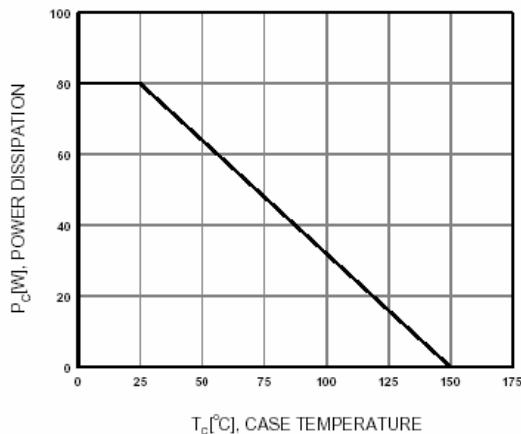


Figure 6. Power Derating